Amplifier Transistors

NPN Silicon

Features

• These are Pb-Free Devices*



Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	50	Vdc
Collector - Base Voltage	V _{CBO}	60	Vdc
Emitter - Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	I _C	100	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	350 2.8	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.0 8.0	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

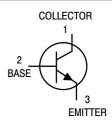
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	125	°C/W

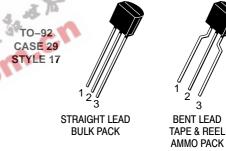
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



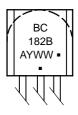
ON Semiconductor®

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MARKING DIAGRAM



A = Assembly Location

Y = Year WW = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BC182G	TO-92 (Pb-Free)	5000 Units / Bulk
BC182BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC182BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage ($I_C = 2.0 \text{ mA}, I_B = 0$)	V _(BR) CEO	50	_	_	V
Collector – Base Breakdown Voltage ($I_C = 10 \mu A, I_E = 0$)	V _{(BR)CBO}	60	_	_	V
Emitter – Base Breakdown Voltage ($I_E = 100 \mu A, I_C = 0$)	V _{(BR)EBO}	6.0	_	_	V
Collector Cutoff Current (V _{CB} = 50 V, V _{BE} = 0)	I _{CBO}	-	0.2	15	nA
Emitter–Base Leakage Current (V _{EB} = 4.0 V, I _C = 0)	I _{EBO}	-	-	15	nA
ON CHARACTERISTICS		1	•	•	
DC Current Gain (I _C = 10 μ A, V _{CE} = 5.0 V) BC18	h _{FE}	40	_	_	-
$(I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V})$ BC18 BC182		120 180	-	500 500	
$(I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V})$ BC18	2	80	-	-	
Collector – Emitter On Voltage ($I_C = 10$ mA, $I_B = 0.5$ mA) ($I_C = 100$ mA, $I_B = 5.0$ mA) (Note 1)	V _{CE(sat)}	C 1/2	0.07 0.2	0.25 0.6	V
Base – Emitter Saturation Voltage (I _C = 100 mA, I _B = 5.0 mA) (Note 1)	V _{BE(sat)}	_	_	1.2	V
Base–Emitter On Voltage $ \begin{array}{l} (I_C=100~\mu\text{A},~V_{CE}=5.0~\text{V})\\ (I_C=2.0~\text{mA},~V_{CE}=5.0~\text{V})\\ (I_C=100~\text{mA},~V_{CE}=5.0~\text{V})~(\text{Note 1}) \end{array} $	V _{BE} (on)	_ 0.55 _	0.5 0.62 0.83	- 0.7 -	V
DYNAMIC CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 0.5$ mA, $V_{CE} = 3.0$ V, $f = 100$ MHz) ($I_C = 10$ mA, $V_{CE} = 5.0$ V, $f = 100$ MHz)	f _T	_ 150	100 200		MHz
Common Base Output Capacitance $(V_{CB} = 10 \text{ V}, I_C = 0, f = 1.0 \text{ MHz})$	C _{ob}	-	_	5.0	pF
Common Base Input Capacitance (V _{EB} = 0.5 V, I _C = 0, f = 1.0 MHz)	C _{ib}	_	8.0	_	pF
Small–Signal Current Gain ($I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$) BC18 BC182		125 240	- -	500 500	-
Noise Figure (I _C = 0.2 mA, V _{CE} = 5.0 V, R _S = 2.0 k Ω , f = 1.0 kHz)	NF	_	2.0	10	dB

^{1.} Pulse Test: Tp 300 s, Duty Cycle 2.0%.

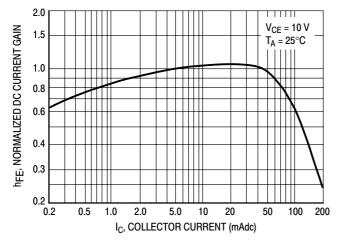


Figure 1. Normalized DC Current Gain

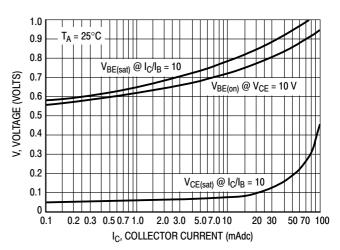


Figure 1. "Saturation" and "On" Voltages

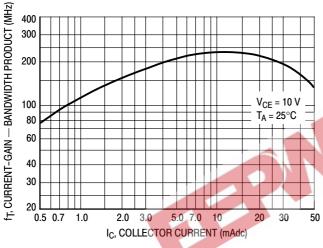


Figure 2. Current-Gain — Bandwidth Product

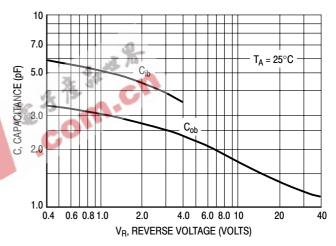


Figure 3. Capacitances

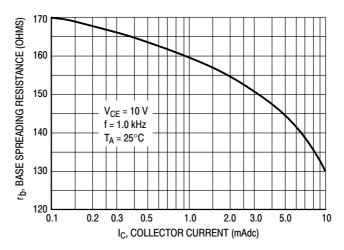
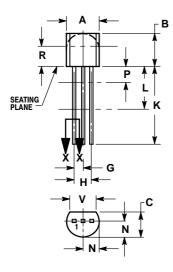


Figure 4. Base Spreading Resistance

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AM



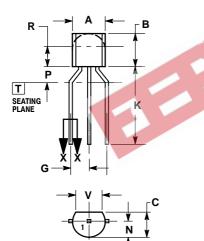
STRAIGHT LEAD **BULK PACK**



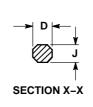
NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R
- IS UNCONTROLLED.
 LEAD DIMENSION IS UNCONTROLLED IN P AND
 BEYOND DIMENSION K MINIMUM.

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		INCHES		MILLIN	IETERS
	DIM	MIN	MAX	MIN	MAX
	Α	0.175	0.205	4.45	5.20
	В	0.170	0.210	4.32	5.33
	С	0.125	0.165	3.18	4.19
	D	0.016	0.021	0.407	0.533
	G	0.045	0.055	1.15	1.39
	Н	0.095	0.105	2.42	2.66
	J	0.015	0.020	0.39	0.50
	K	0.500		12.70	
•	L	0.250		6.35	
	N	0.080	0.105	2.04	2.66
	P		0.100		2.54
X	R	0.115		2.93	
	V	0.135		3.43	
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and the second s		: MENSION	IING AND	TOI EDA	NCING DI



BENT LEAD TAPE & REEL AMMO PACK



- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM

	MILLIMETERS			
DIM	MIN	MAX		
Α	4.45	5.20		
В	4.32	5.33		
С	3.18	4.19		
D	0.40	0.54		
G	2.40	2.80		
J	0.39	0.50		
K	12.70			
N	2.04	2.66		
P	1.50	4.00		
R	2.93			
٧	3.43			

STYLE 17:

PIN 1. COLLECTOR

BASE EMITTER

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